

15V 19mohm P-channel Trench MOSFET
AKT15P230EL

Description:

This P channel Trench MOSFET was designed for DC-DC converter and electric smoker.

Features:

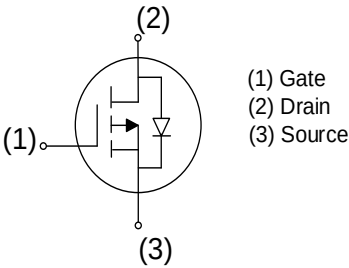
- RoHS compliant ^(Note 1)
- Halogen-free ^(Note 1)

Applications:

- DC-DC Converter
- Electric Smoker

Key Performance Parameters:

Parameter	Value	Unit
V _{DS}	-15	V
R _{DS(on)} , max @V _{GS} = -4.5 V	19	mΩ
I _D	-7	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AKT15P230EL	SOT-23-3L	T15P230EL	Tape Reel	See the detail package information

Notes:

1. Contact ALKAIDSEMI sales for detail information

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	-15	V
I_D	Drain Current - Continuous ($T_A = 25^\circ\text{C}$) ^(Note 1)	-7	A
	Drain Current - Continuous ($T_A = 100^\circ\text{C}$)	-4.5	A
I_{DM}	Drain Current - Pulsed ^(Note 2)	-28	A
V_{GS}	Gate-Source Voltage	± 12	V
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)	1.3	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Steady State ^(Note 3)	97	$^\circ\text{C/W}$

Notes:

1. Continuous current based on $R_{\theta JA}$
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. Mount on minimum PCB layout

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Static Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-15			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V},$			-1	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
$V_{GS(TH)}$	Gate Threshold voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.5	-0.7	-1.2	V
$R_{DS(ON)}$	Drain-Source on-state resistance	$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		14	19	m Ω
		$V_{GS} = -2.5\text{ V}, I_D = -4\text{ A}$		19	25	m Ω

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V},$ $F = 1\text{ MHz}$		1940		pF
C_{OSS}	Output Capacitance			387		pF
C_{RSS}	Reverse Transfer Capacitance			347		pF
R_G	Gate Resistance	$F = 1\text{ MHz}$		10.3		Ω

Switching Characteristics

$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = -6\text{ V}, R_L = 0.9\text{ }\Omega,$ $V_{GS} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		24		ns
T_R	Rise Time			101.5		ns
$T_{D(OFF)}$	Turn Off Delay Time			291		ns
T_F	Fall Time			157		ns
Q_G	Total Gate Charge	$V_{DD} = -6\text{ V}, I_D = -7\text{ A},$ $V_{GS} = -4.5\text{ V}$		19		nC
Q_{GS}	Gate-Source Charge			9		nC
Q_{GD}	Gate-Drain Charge			4.5		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Body-Diode Forward Current			-7	A
I_{SM}	Maximum Pulsed Body-Diode Forward Current			-28	A
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1\text{ A}$		-0.7	V

Electrical Characteristics Diagrams

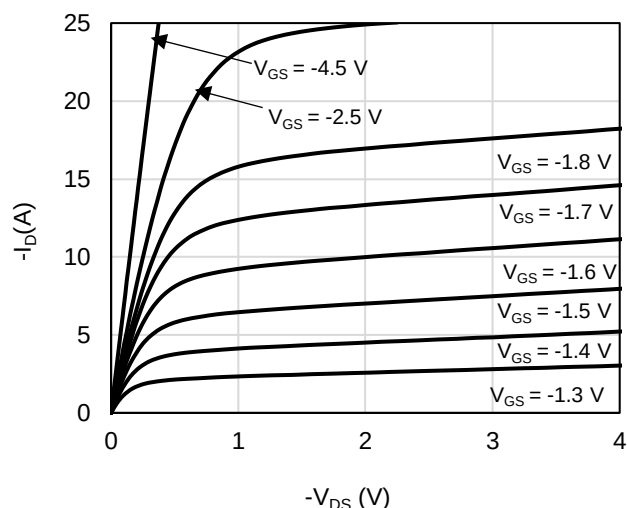


Figure 1: On-Region Characteristics

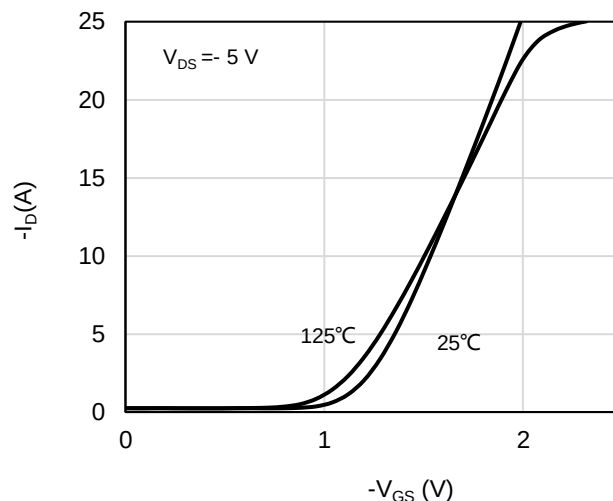


Figure 2: Transfer Characteristics

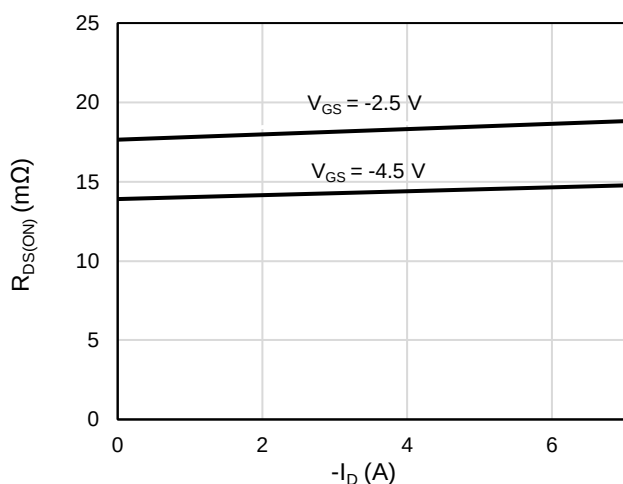


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

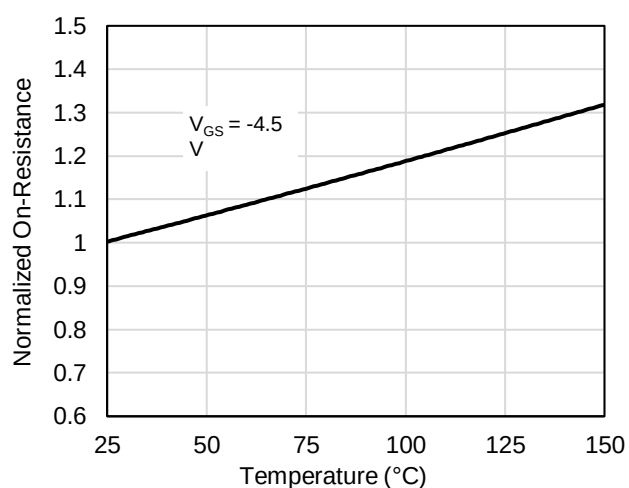


Figure 4: On-Resistance vs. Junction Temperature

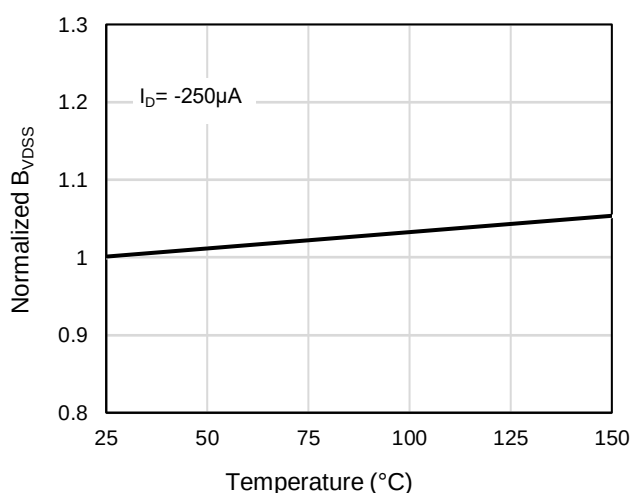


Figure 5: Breakdown Voltage vs. Junction Temperature

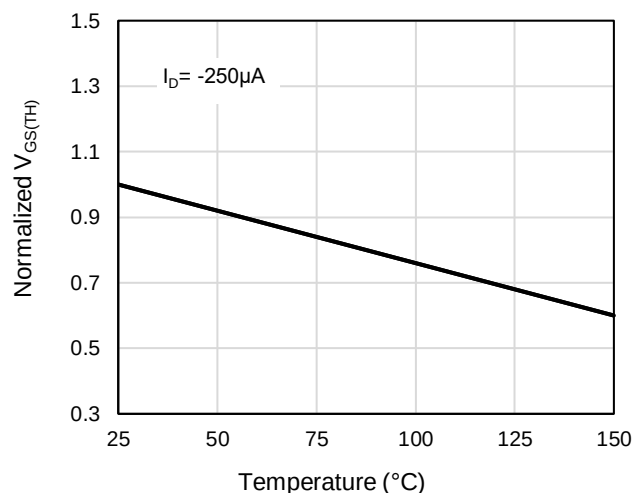
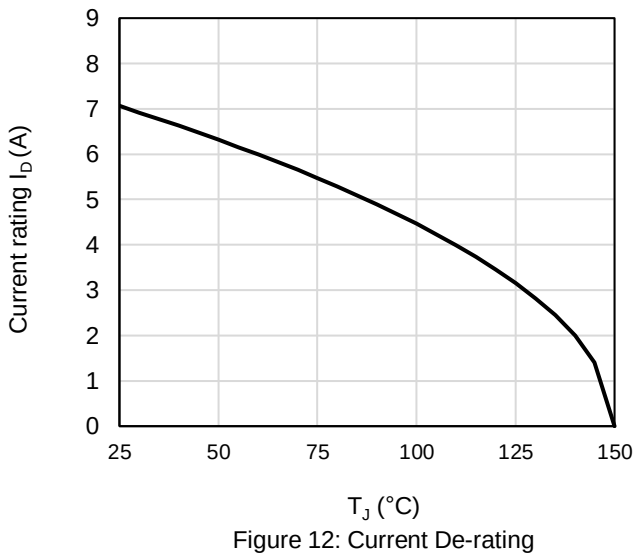
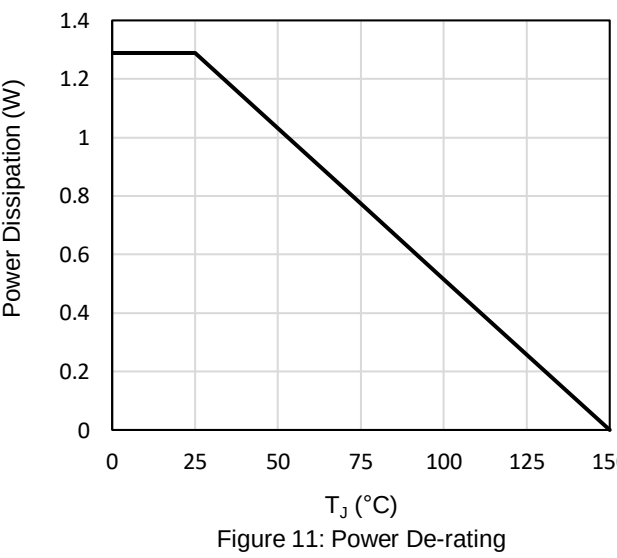
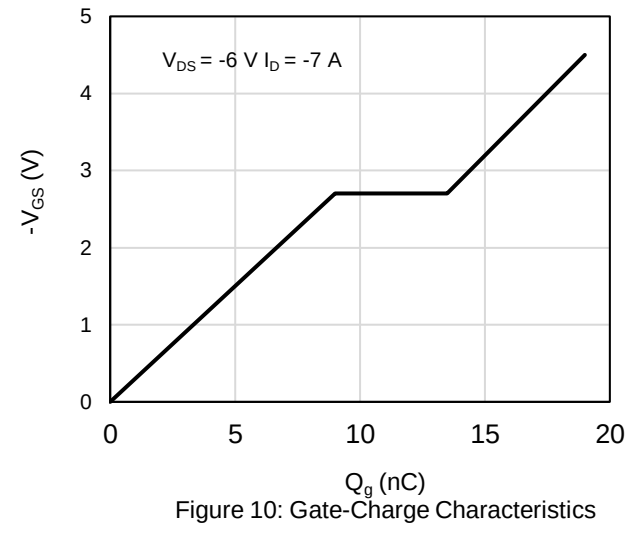
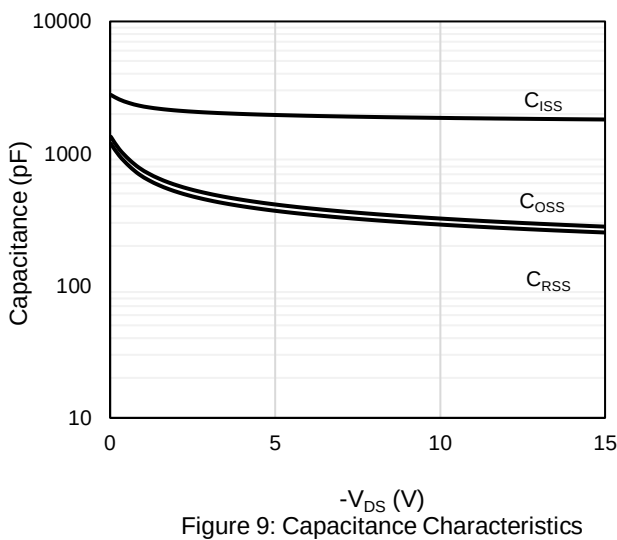
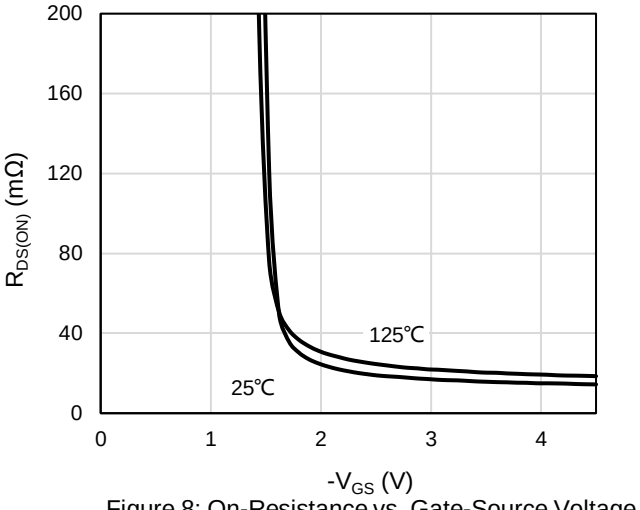
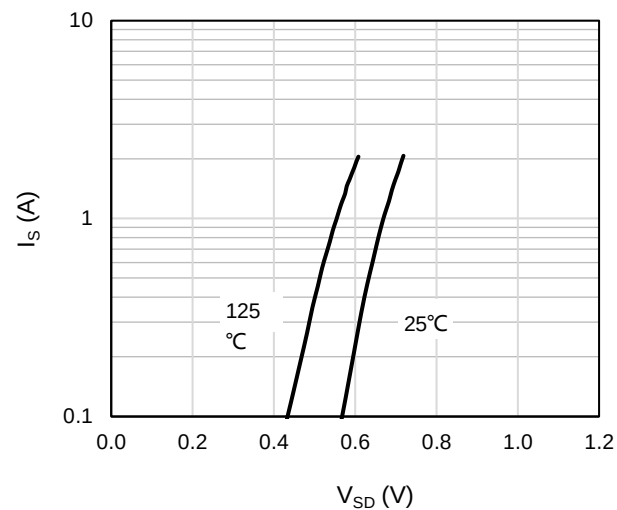


Figure 6: Threshold Voltage vs. Junction Temperature



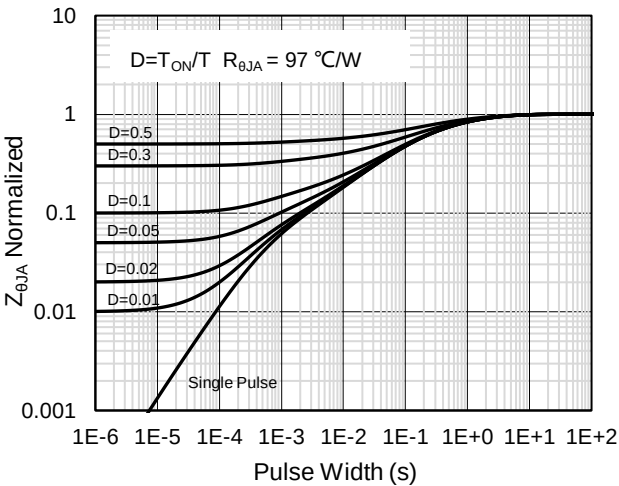


Figure 13: Normalized Maximum Transient Thermal Impedance

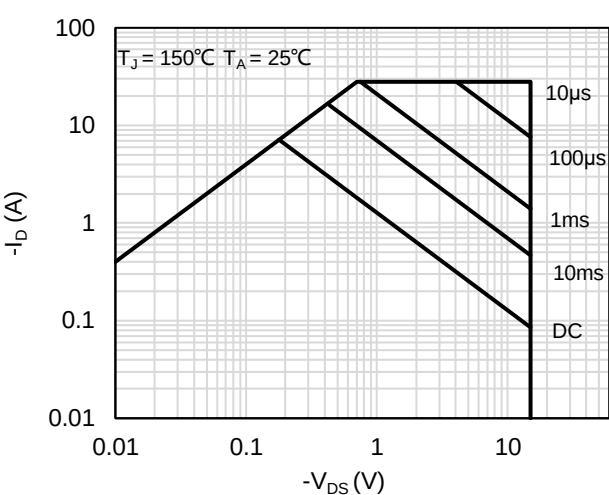
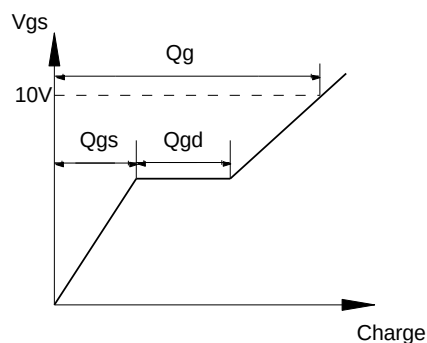
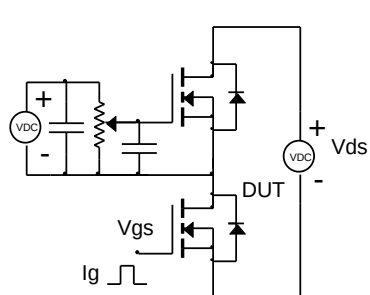


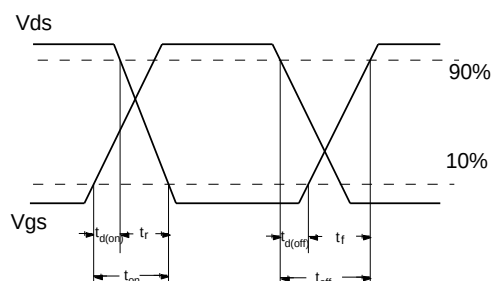
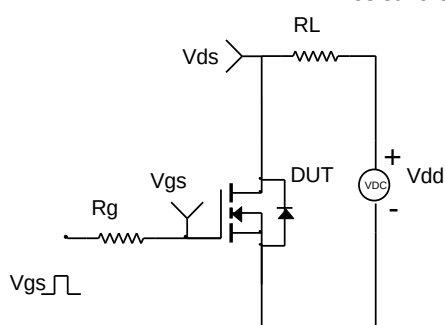
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

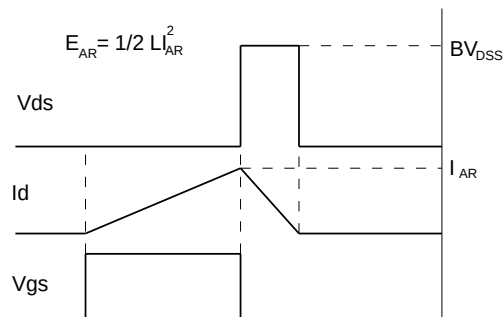
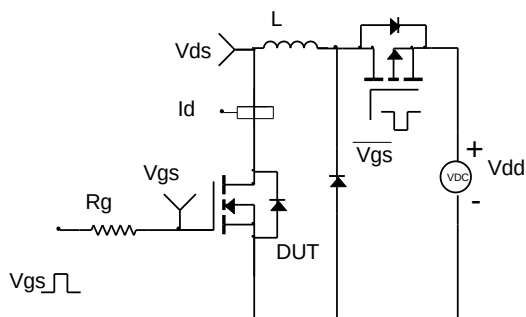
Gate Charge Test Circuit & Waveform



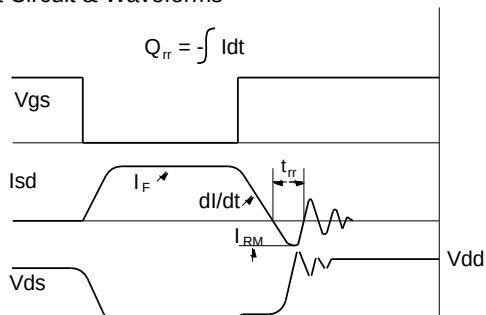
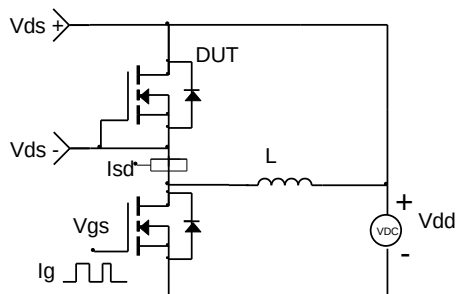
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History

Revision	Release Date	Remark
Rev.1.1	2023/4/6	

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.